Abstracts

Yield Considerations for Ion Implanted GaAs MMICs (1982 [MCS])

A.K. Gupta, W.C. Petersen and D.R. Decker. "Yield Considerations for Ion Implanted GaAs MMICs (1982 [MCS])." 1982 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 82.1 (1982 [MCS]): 31-35.

An ion implantation based process is described for fabricating GaAs Monolithic Microwave Integrated Circuits (MMICs) incorporating active devices, RF circuitry and bypass capacitors. Low ohmic contact resistance and good control of metal-insulator-metal (MIM) capacitance values is demonstrated and some factors affecting FET and capacitor yield are discussed. High DC yield of typical amplifier circuits is shown indicating that this process has the potential for achieving very high overall yields in a production environment. Good yield of functional MMIC modules with subsystem complexity is projected.

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